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Lead-free Green

DMP2065U

20V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	Package	I_D max T_A = +25°C
-20V	60mΩ @ V_{GS} = -4.5V	SOT-23	-4.0A
	90mΩ @ V_{GS} = -2.5V		-3.3A

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

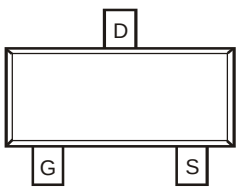
This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Mechanical Data

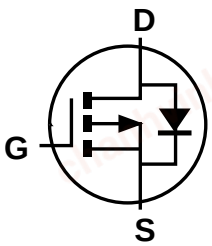
- Case: SOT23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208 e3
- Lead-Free Plating (Matte Tin Finish Annealed over Alloy 42 Lead-Frame).
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)



Top View



Top View
Pin Configuration



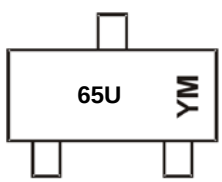
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2065U-7	SOT23	3000/Tape & Reel
DMP2065U-13	SOT23	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



65U = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: H = 2020)
M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026
Code	H	I	J	K	L	M	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@ T_A = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-20	V
Gate-Source Voltage			V_{GSS}	±12	V
Drain Current (Note 6) V_{GS} = -4.5V	Steady State	T_A = +25°C	I_D	-4.0	A
		T_A = +70°C		-3.0	
Pulsed Drain Current (Pulse width ≤10µS, Duty Cycle ≤1%)			I_{DM}	-15	A

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	138	°C/W
Total Power Dissipation (Note 6)		P_D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	83	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C unless otherwise specified.)

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage		BV_{DSS}	-20	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current	T_J = +25°C	I_{DSS}	—	—	-1.0	µA	V_{DS} = -20V, V_{GS} = 0V
Gate-Source Leakage		I_{GSS}	—	—	±50	nA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage		$V_{GS(th)}$	-0.5	—	-0.9	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance		$R_{DS\ (ON)}$	—	41	60	mΩ	V_{GS} = -4.5V, I_D = -4.2A
				53	90		V_{GS} = -2.5V, I_D = -3.4A
				72	113		V_{GS} = -1.8V, I_D = -2.0A
Diode Forward Voltage		V_{SD}	—	-0.7	-1.1	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance		C_{iss}	—	808	—	pF	V_{DS} = -15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance		C_{oss}	—	85	—	pF	
Reverse Transfer Capacitance		C_{rss}	—	77	—	pF	
Gate Resistance		R_G	—	15.2	—	Ω	V_{GS} = 0V, V_{DS} = 0V, f = 1.0MHz
Total Gate Charge		Q_g	—	10.2	—	nC	V_{GS} = -4.5V, V_{DS} = -4V, I_D = -3.5A
Gate-Source Charge		Q_{gs}	—	1.3	—	nC	
Gate-Drain Charge		Q_{gd}	—	2.2	—	nC	
Turn-On Delay Time		$t_{D(on)}$	—	10.8	—	ns	V_{DS} = -4V, V_{GS} = -4.5V, R_L = 4Ω, R_G = 6Ω, I_D = -1A
Turn-On Rise Time		t_r	—	13.7	—	ns	
Turn-Off Delay Time		$t_{D(off)}$	—	79.3	—	ns	
Turn-Off Fall Time		t_f	—	34.7	—	ns	

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1in. square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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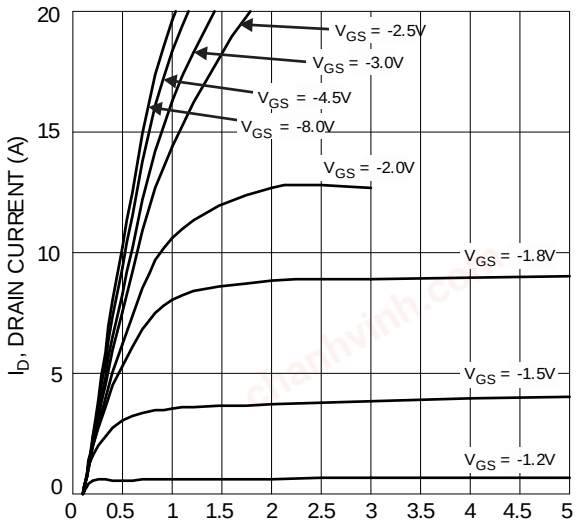


Figure 1 Typical Output Characteristics

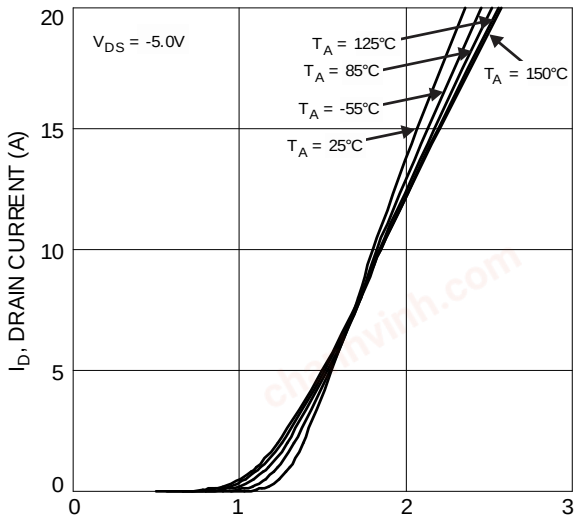


Figure 2 Typical Transfer Characteristics

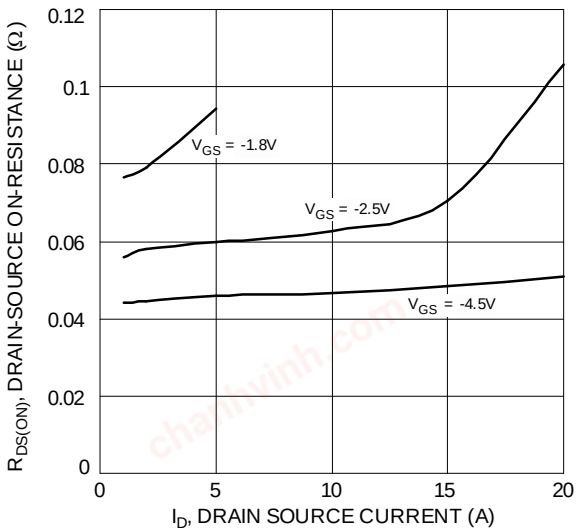


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

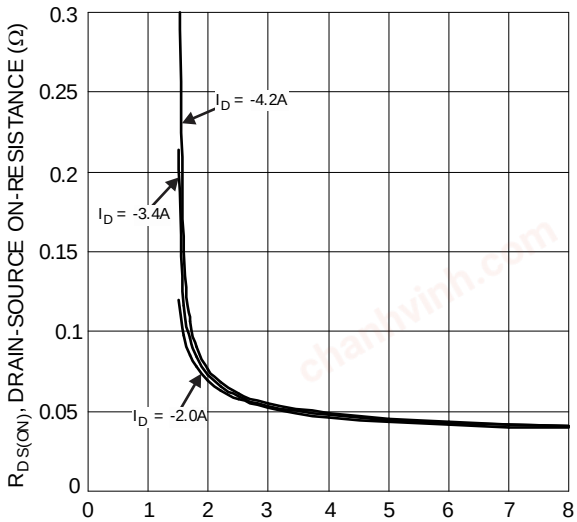


Figure 4 Typical Transfer Characteristics

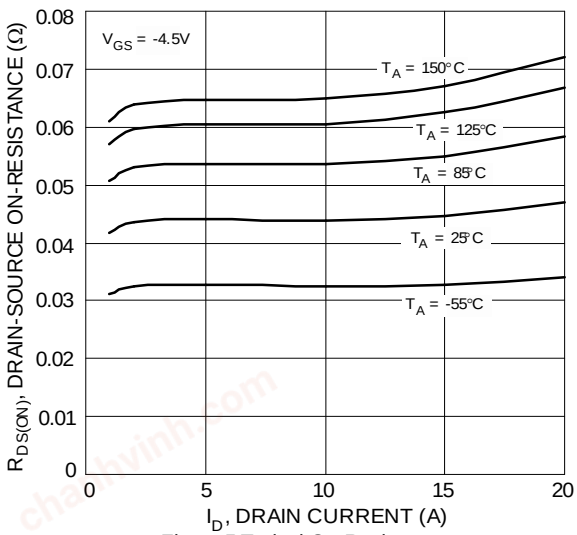


Figure 5 Typical On-Resistance vs. Drain Current and Junction Temperature

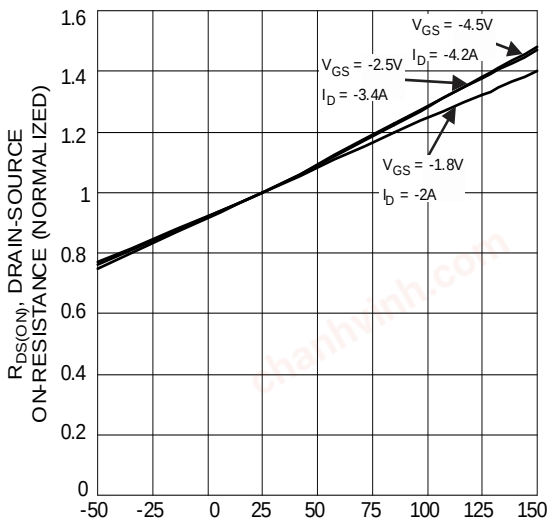


Figure 6 On-Resistance Variation with Junction Temperature

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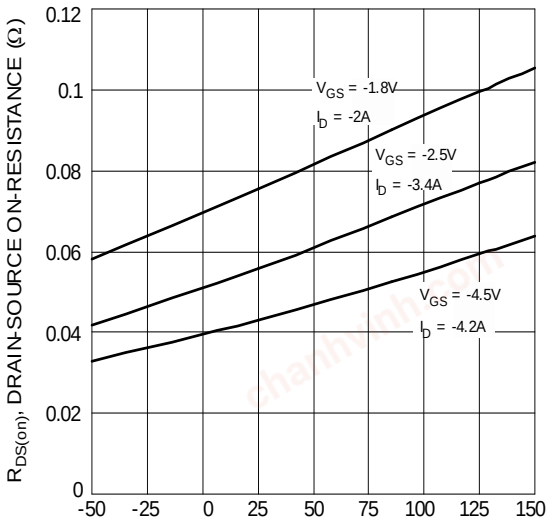


Figure 7 On-Resistance Variation with Junction Temperature

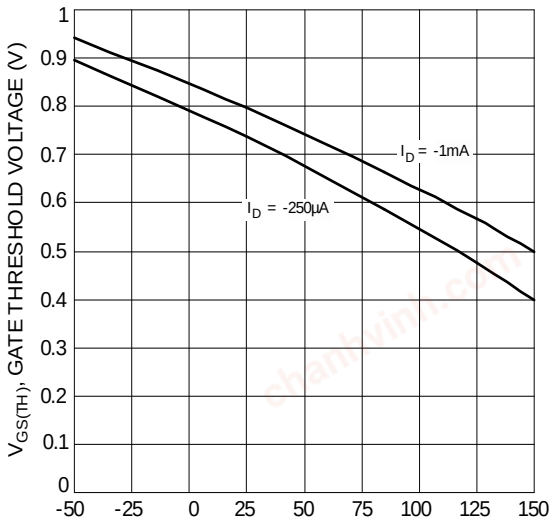


Figure 8 Gate Threshold Variation vs. Junction Temperature

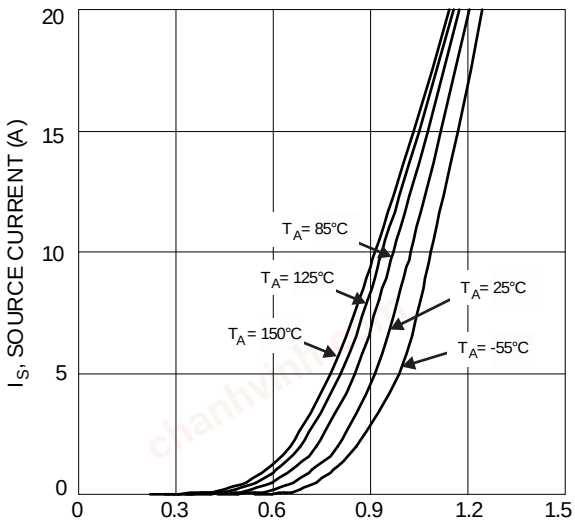


Figure 9 Diode Forward Voltage vs. Current

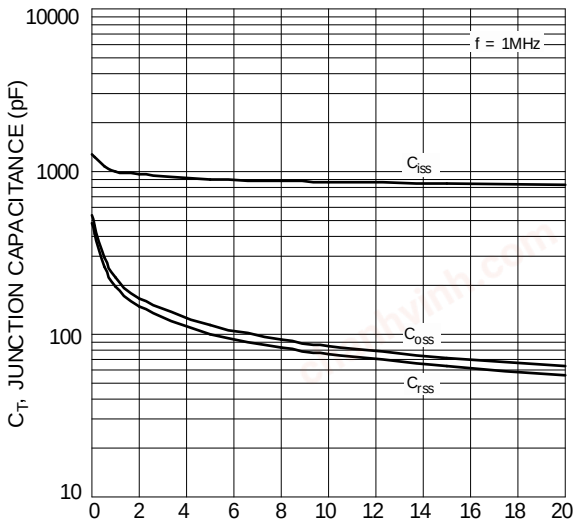


Figure 10 Typical Junction Capacitance

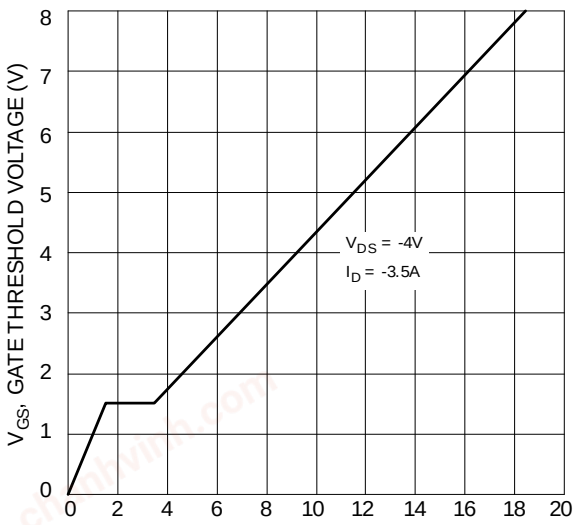


Figure 11 Gate Charge

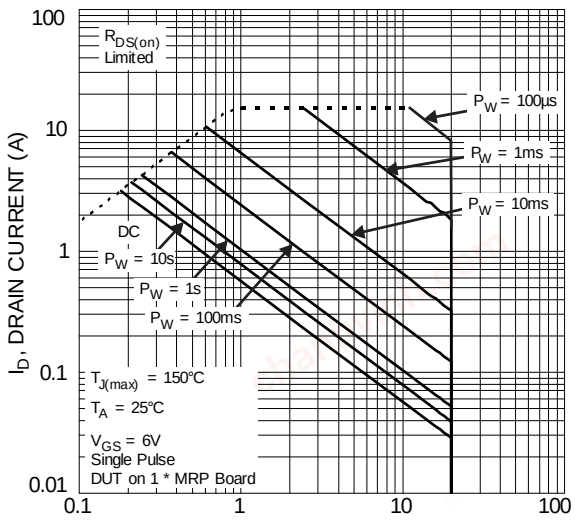


Figure 12 SOA, Safe Operation Area

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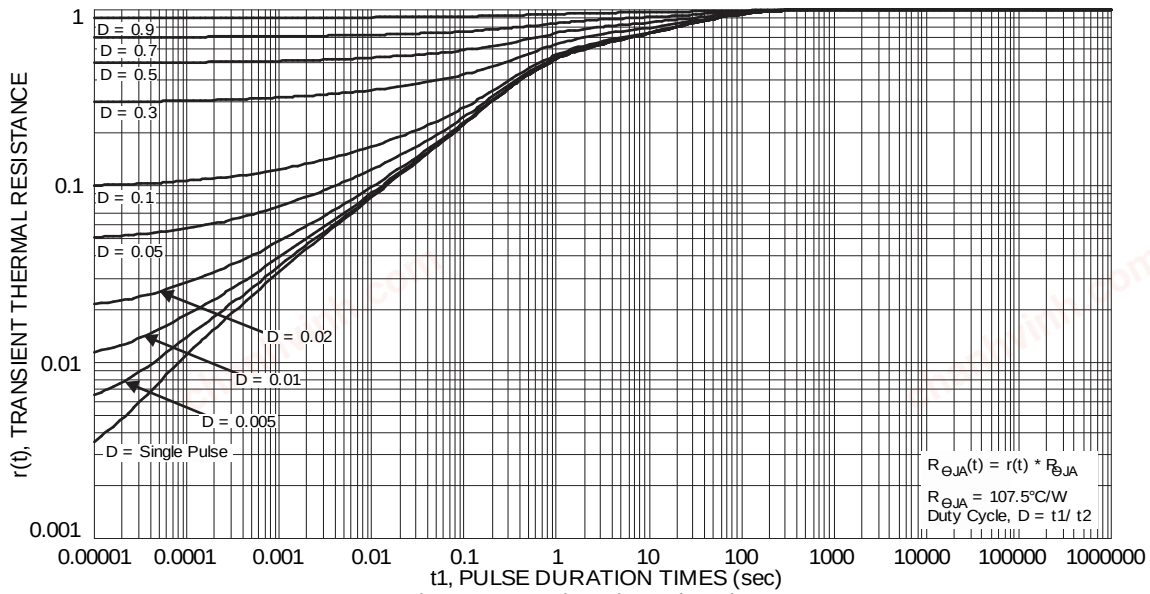


Figure 15 Transient Thermal Resistance

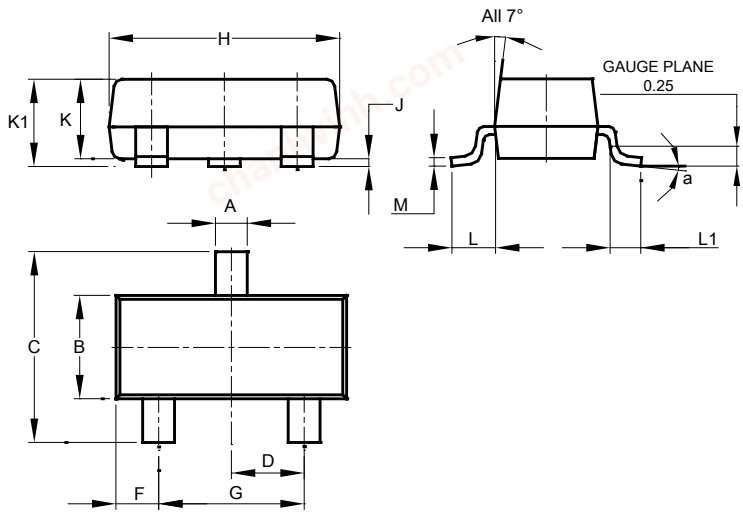
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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

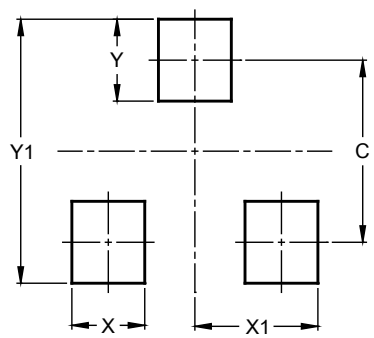


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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